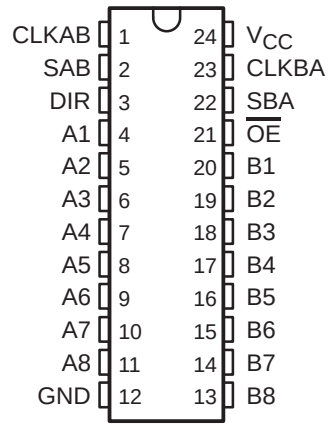
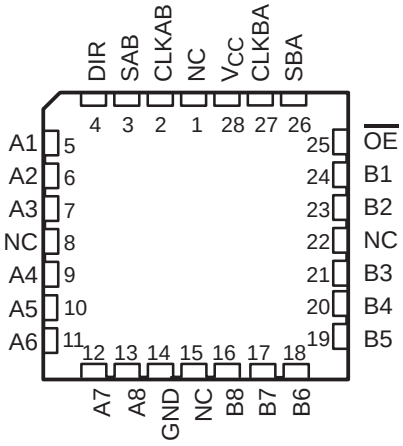
- **State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static Power Dissipation**
- **Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V_{CC})**
- **Support Unregulated Battery Operation Down to 2.7 V**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Bus-Hold Data Inputs Eliminate the Need for External Pullup Resistors**
- **Support Live Insertion**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (JT) DIPs**

SN54LVT646 . . . JT OR W PACKAGE
SN74LVT646 . . . DB, DW, OR PW PACKAGE
(TOP VIEW)



SN54LVT646 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

These bus transceivers and registers are designed specifically for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment.

The ’LVT646 consist of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers. Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the ′LVT646.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs are provided to control the transceiver functions. In the transceiver mode, data present at the high-impedance port may be stored in either register or in both.

The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The direction control (DIR) determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data may be stored in one register and/or B data may be stored in the other register.

When an output function is disabled, the input function is still enabled and may be used to store and transmit data. Only one of the two buses, A or B, may be driven at a time.

description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

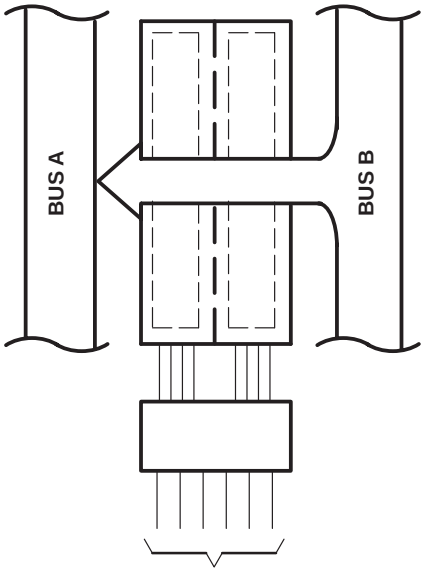
The SN74LVT646 is available in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN54LVT646 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LVT646 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

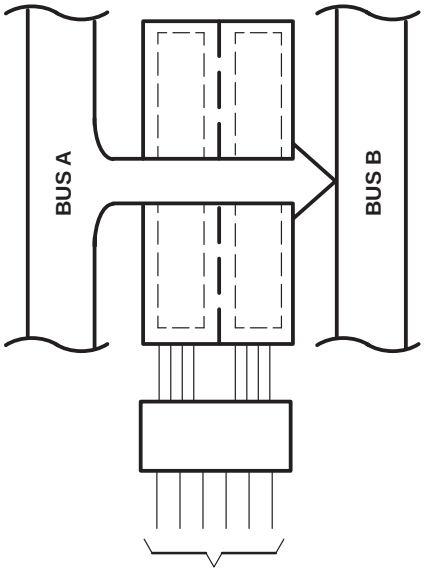
INPUTS						DATA I/Os		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
X	X	↑	X	X	X	Input	Unspecified†	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified†	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input disabled	Input disabled	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B bus
L	H	H or L	X	H	X	Input	Output	Stored A data to B bus

† The data output functions may be enabled or disabled by various signals at the $\overline{OE}$ and DIR inputs. Data input functions are always enabled; i.e., data at the bus pins is stored on every low-to-high transition of the clock inputs.



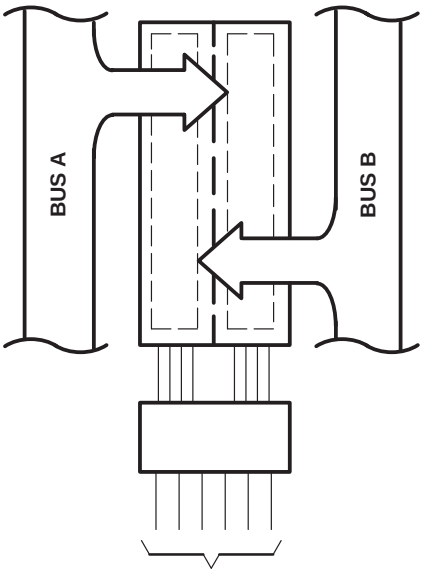
21 $\overline{OE}$	3 DIR	1 CLKAB	23 CLKBA	2 SAB	22 SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



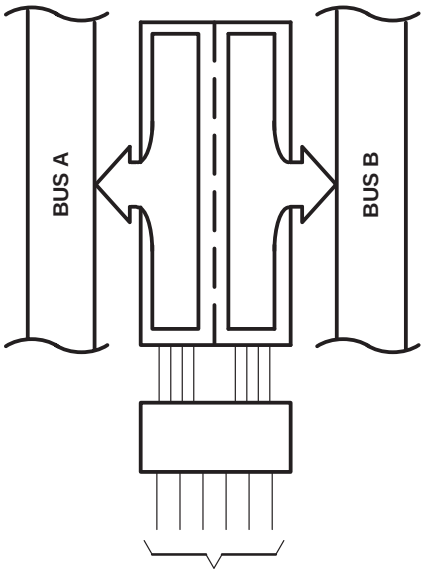
21 $\overline{OE}$	3 DIR	1 CLKAB	23 CLKBA	2 SAB	22 SBA
L	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



21 $\overline{OE}$	3 DIR	1 CLKAB	23 CLKBA	2 SAB	22 SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B



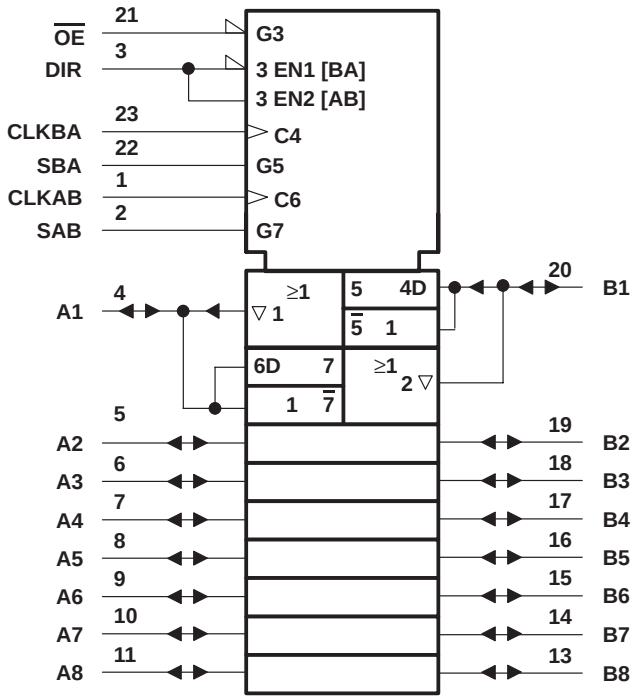
21 $\overline{OE}$	3 DIR	1 CLKAB	23 CLKBA	2 SAB	22 SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA
TO A AND/OR B

Figure 1. Bus-Management Functions

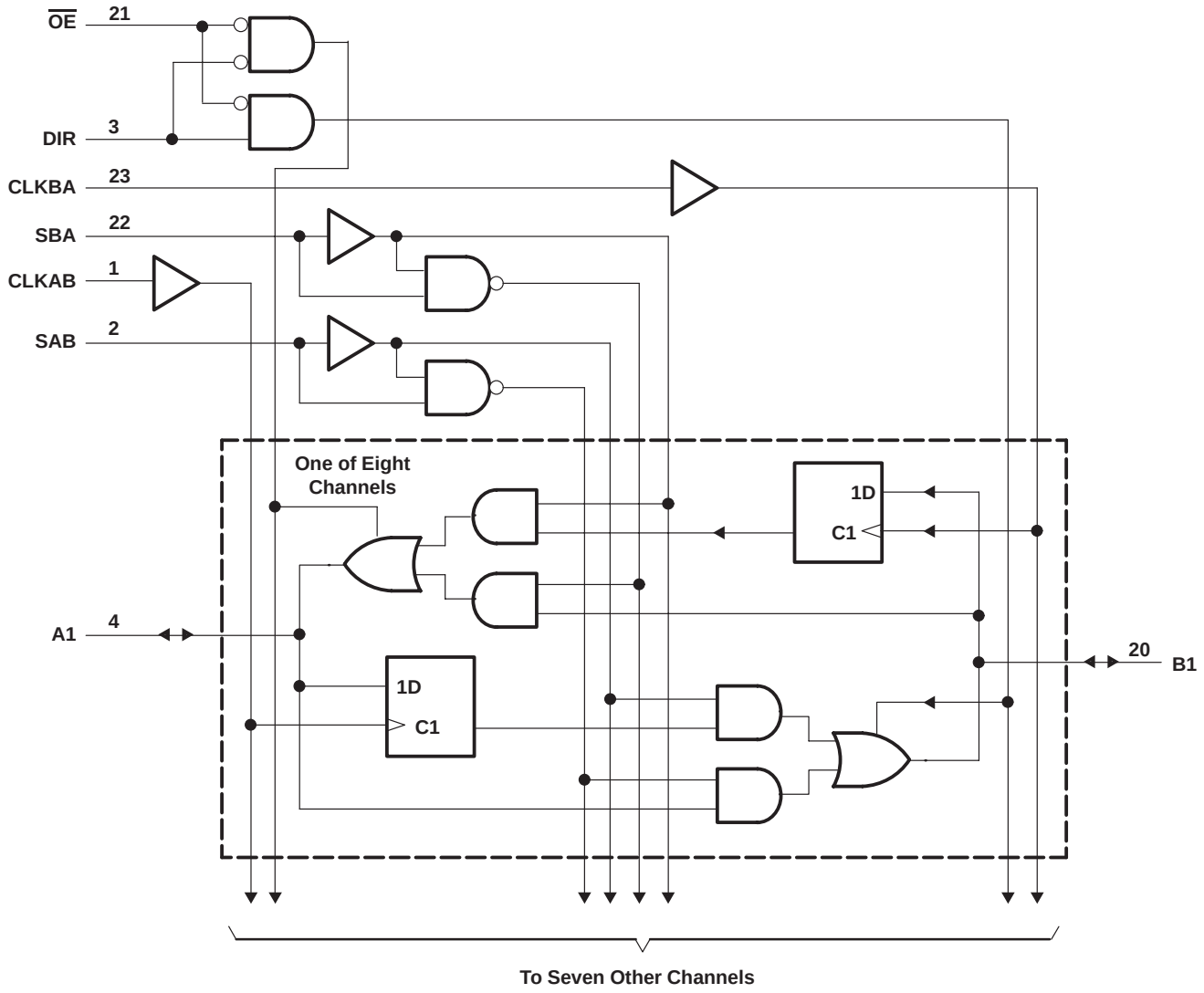
Pin numbers shown are for the DB, DW, JT, PW, and W packages.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the DB, DW, JT, PW, and W packages.

logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, PW, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high state or power-off state, V_O (see Note 1) . . . . –0.5 V to 7 V
Current into any output in the low state, I_O: SN54LVT646 . . . . . 96 mA
SN74LVT646 . . . . . 128 mA
Current into any output in the high state, I_O (see Note 2): SN54LVT646 . . . . . 48 mA
SN74LVT646 . . . . . 64 mA
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package . . . . . 0.65 W
DW package . . . . . 1.7 W
PW package . . . . . 0.7 W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			SN54LVT646		SN74LVT646		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		2.7	3.6	2.7	3.6	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage			5.5		5.5	V
I_{OH}	High-level output current			–24		–32	mA
I_{OL}	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 4: Unused control inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			SN54LVT646			SN74LVT646			UNIT
				MIN	TYP†	MAX	MIN	TYP†	MAX	
V_{IK}	V_{CC} = 2.7 V,	I_I = –18 mA				–1.2			–1.2	V
V_{OH}	V_{CC} = MIN to MAX‡,	I_{OH} = –100 µA		V_{CC}–0.2			V_{CC}–0.2			V
	V_{CC} = 2.7 V,	I_{OH} = – 8 mA		2.4			2.4			
	V_{CC} = 3 V	I_{OH} = – 24 mA		2						
		I_{OH} = –32 mA					2			
V_{OL}	V_{CC} = 2.7 V	I_{OL} = 100 µA				0.2			0.2	V
		I_{OL} = 24 mA				0.5			0.5	
	V_{CC} = 3 V	I_{OL} = 16 mA				0.4			0.4	
		I_{OL} = 32 mA				0.5			0.5	
		I_{OL} = 48 mA				0.55				
		I_{OL} = 64 mA							0.55	
I_I	V_{CC} = 3.6 V,	V_I = V_{CC} or GND	Control inputs			±1			±1	µA
	V_{CC} = 0 or MAX‡,	V_I = 5.5 V				10			10	
	V_{CC} = 3.6 V	V_I = 5.5 V	A or B ports§			100			20	
		V_I = V_{CC}				1			1	
		V_I = 0				–5			–5	
I_{off}	V_{CC} = 0,	V_I or V_O = 0 to 4.5 V							±100	µA
$I_{I(hold)}$	V_{CC} = 3 V	V_I = 0.8 V	A or B ports	75			75			µA
		V_I = 2 V		–75			–75			
I_{OZH}	V_{CC} = 3.6 V,	V_O = 3 V				1			1	µA
I_{OZL}	V_{CC} = 3.6 V,	V_O = 0.5 V				–1			–1	µA
I_{CC}	V_{CC} = 3.6 V, V_I = V_{CC} or GND	I_O = 0,	Outputs high		0.13	0.39		0.13	0.19	mA
			Outputs low		8.8	14		8.8	12	
			Outputs disabled		0.13	0.39		0.13	0.19	
ΔI_{CC}¶	V_{CC} = 3 V to 3.6 V, Other inputs at V_{CC} or GND	One input at V_{CC} – 0.6 V,				0.3			0.2	mA
C_i	V_I = 3 V or 0				4.5			4.5		pF
C_{io}	V_O = 3 V or 0				11			11		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
§ Unused terminals at V_{CC} or GND
¶ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

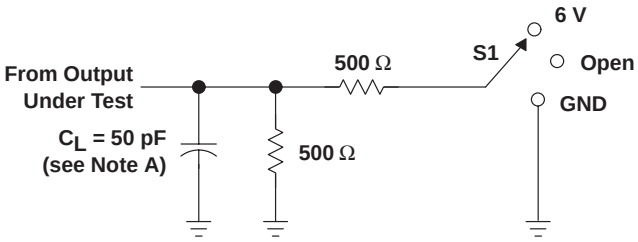
			SN54LVT646				SN74LVT646				UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		0	150	0	150	0	150	0	150	MHz
t_w	Pulse duration, CLK high or low		3.3		3.3		3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	Data high	1.5		1.5		1.3		1.3		ns
		Data low	2.5		3.0		2		2.4		
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑		0.9		0.9		0.4		0.4		ns

switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	SN54LVT646				SN74LVT646					UNIT
			V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V			V_{CC} = 2.7 V		
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
f_{max}			150				150					MHz
t_{PLH}	CLKBA or CLKAB	A or B	1.2	5.9		6.9	1.8	3.8	5.7		6.7	ns
t_{PHL}			1.2	5.9		6.6	2.1	3.8	5.7		6.4	
t_{PLH}	A or B	B or A	0.8	4.9		5.6	1.3	2.8	4.7		5.4	ns
t_{PHL}			0.6	4.8		5.5	1	2.7	4.6		5.3	
t_{PLH}	SBA or SAB‡	A or B	1	6.4		7.4	1.4	3.7	6.2		7.2	ns
t_{PHL}			1	6.4		7	1.4	3.8	6.2		6.8	
t_{PZH}	$\overline{OE}$	A or B	0.6	6		7.4	1	3	5.8		7.2	ns
t_{PZL}			0.6	6.2		7.5	1	3.2	6		7.3	
t_{PHZ}	$\overline{OE}$	A or B	1.4	6.7		7.1	2.3	4.3	6.5		6.9	ns
t_{PLZ}			1.4	6.4		6.5	2.2	3.8	5.8		5.9	
t_{PZH}	DIR	A or B	0.6	6.7		7.7	1	3.4	6.5		7.5	ns
t_{PZL}			0.8	6.5		7.3	1.2	3.4	6.3		7.1	
t_{PHZ}	DIR	A or B	0.8	7.4		8.3	1.7	4.1	7.2		8.1	ns
t_{PLZ}			1	6.7		7	1.5	3.5	5.8		6.3	

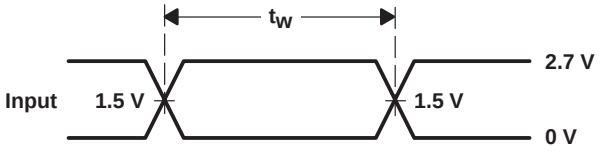
† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ These parameters are measured with the internal output state of the storage register opposite to that of the bus input.

PARAMETER MEASUREMENT INFORMATION

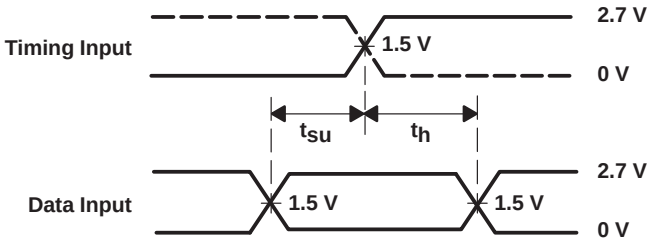


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

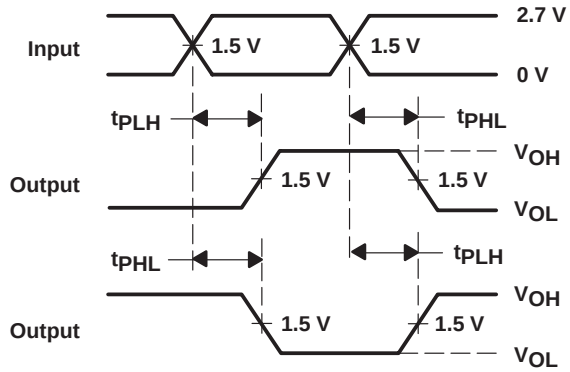
LOAD CIRCUIT FOR OUTPUTS



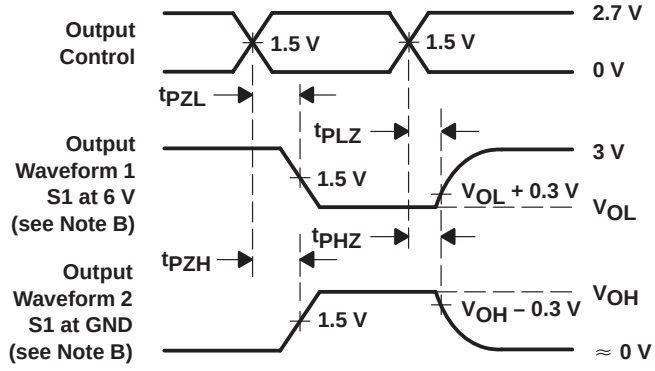
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.